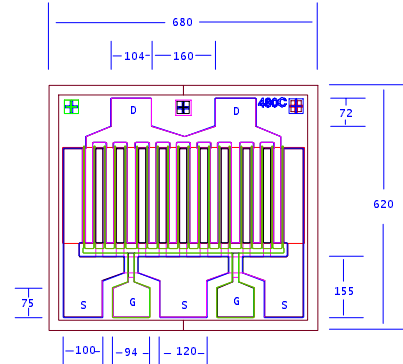


**PRELIMINARY DATA SHEET**
**Low Distortion GaAs Power FET**

- +33.5dBm TYPICAL OUTPUT POWER
- 18.0dB TYPICAL POWER GAIN AT 2GHz
- High BV<sub>gd</sub> FOR 10V BIAS
- 0.5 X 4800 MICRON RECESSED “MUSHROOM” GATE
- Si<sub>3</sub>N<sub>4</sub> PASSIVATION AND PLATED HEAT SINK
- ADVANCED EPITAXIAL DOPING PROFILE PROVIDES HIGH POWER EFFICIENCY, LINEARITY AND RELIABILITY
- Id<sub>ss</sub> SORTED IN 80mA PER BIN RANGE



Chip Thickness: 75 ± 13 microns  
All Dimensions In Microns

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub> = 25 °C)**

SYMBOLS	PARAMETERS/TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>P<sub>1dB</sub></b>	Output Power at 1dB Compression V <sub>ds</sub> =8V, I <sub>ds</sub> =50% I <sub>ds</sub>	f= 2GHz 32.0	f= 2GHz 33.5		dBm
		f= 4GHz	33.5		
<b>G<sub>1dB</sub></b>	Gain at 1dB Compression V <sub>ds</sub> =8V, I <sub>ds</sub> =50% I <sub>ds</sub>	f= 2GHz 16.0	f= 2GHz 18.0		dB
		f= 4GHz	12.5		
<b>PAE</b>	Gain at 1dB Compression V <sub>ds</sub> =8V, I <sub>ds</sub> =50% I <sub>ds</sub>		f= 2GHz 40		%
<b>I<sub>ds</sub></b>	Saturated Drain Current V <sub>ds</sub> =3V, V <sub>gs</sub> =0V	640	960	1440	mA
<b>G<sub>m</sub></b>	Transconductance V <sub>ds</sub> =3V, V <sub>gs</sub> =0V	200	560		mS
<b>V<sub>p</sub></b>	Pinch-off Voltage V <sub>ds</sub> =3V, I <sub>ds</sub> =10mA		-2.5	-4.0	V
<b>BV<sub>gd</sub></b>	Drain Breakdown Voltage I <sub>gd</sub> =4.8mA	-15	-20		V
<b>BV<sub>gs</sub></b>	Source Breakdown Voltage I <sub>gs</sub> =4.8mA	-10	-17		V
<b>R<sub>th</sub></b>	Thermal Resistance (Au-Sn Eutectic Attach)		12		°C/W

**MAXIMUM RATINGS AT 25°C**

SYMBOLS	PARAMETERS	ABSOLUTE <sup>1</sup>	CONTINUOUS <sup>2</sup>
<b>V<sub>ds</sub></b>	Drain-Source Voltage	14V	10V
<b>V<sub>gs</sub></b>	Gate-Source Voltage	-8V	-4.5V
<b>I<sub>ds</sub></b>	Drain Current	I <sub>ds</sub>	960mA
<b>I<sub>gsf</sub></b>	Forward Gate Current	120mA	20mA
<b>P<sub>in</sub></b>	Input Power	32dBm	@3dB Compression
<b>T<sub>ch</sub></b>	Channel Temperature	175°C	150°C
<b>T<sub>stg</sub></b>	Storage Temperature	-65/175°C	-65/150°C
<b>P<sub>t</sub></b>	Total Power Dissipation	11.4 W	9.5 W

Note: 1. Exceeding any of the above ratings may result in permanent damage.

2. Exceeding any of the above ratings may reduce MTTF below design goals.

# EFC480C

## PRELIMINARY DATA SHEET

### Low Distortion GaAs Power FET

#### S-PARAMETERS

10V, 1/2 Idss

Freq GHz	---S11---		---S21---		---S12---		---S22---	
	Mag	Ang	Mag	Ang	Mag	Ang	Mag	Ang
0.500	0.937	-106.2	10.161	120.8	0.022	35.8	0.518	-166.8
1.000	0.897	-134.9	6.389	104.7	0.028	26.4	0.505	-168.3
1.500	0.897	-151.8	4.443	93.5	0.028	21.5	0.524	-171.2
2.000	0.897	-161.0	3.370	85.4	0.029	19.0	0.533	-173.0
2.500	0.898	-167.2	2.695	79.2	0.030	20.2	0.539	-173.8
3.000	0.895	-171.8	2.231	73.9	0.030	19.5	0.542	-174.2
3.500	0.890	-175.4	1.894	69.4	0.030	20.9	0.542	-173.9
4.000	0.850	-176.6	1.654	66.9	0.026	27.6	0.560	-172.2
4.500	0.901	177.7	1.535	59.9	0.032	23.1	0.607	-169.5
5.000	0.899	174.5	1.357	55.2	0.031	25.8	0.617	-170.8
5.500	0.900	172.5	1.208	51.4	0.031	28.1	0.620	-171.8
6.000	0.901	170.8	1.087	48.2	0.031	30.4	0.619	-172.8
6.500	0.902	169.6	0.999	45.8	0.032	32.0	0.616	-172.6
7.000	0.893	168.8	0.941	43.3	0.033	37.1	0.637	-171.2
7.500	0.904	170.7	0.916	39.2	0.037	34.8	0.669	-172.8
8.000	0.919	169.5	0.840	34.2	0.036	35.0	0.681	-175.0
8.500	0.918	169.2	0.783	31.0	0.038	36.6	0.693	-176.9
9.000	0.924	168.7	0.729	27.9	0.037	37.6	0.701	-178.6
9.500	0.927	168.0	0.687	24.5	0.038	39.8	0.706	-179.3
10.000	0.932	167.3	0.647	22.3	0.040	42.4	0.716	179.8

Note: The data included 0.7 mils diameter Au bonding wires:  
2 gate wires, 20 mils each; 2 drain wires, 12 mils each; 6 source wires, 7 mils each.